

Miniature-package Crystal Oscillator Module ICs

OVERVIEW

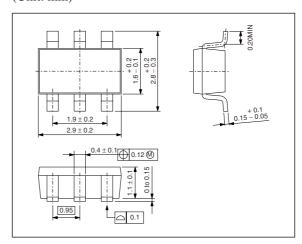
The SM5023 series are 3rd overtone crystal oscillator module ICs. They feature built-in oscillator capacitors with excellent frequency response. As cutoff frequency can be configured by using an external feedback resistor $R_{\rm fo}$, a favorable 3rd overtone oscillation can be realized with a few external components. The oscillator circuit characteristics are optimized for a 3rd overtone oscillation by round blank. They also feature a built-in output buffer with high output drive capability and are available in miniature 6-pin package, making them ideal as DIP-type crystal oscillators.

FEATURES

- Operating supply voltage range
 - 3V operation: 2.7 to 3.6V
 - 5V operation: 4.5 to 5.5V
- 4MHz to 70MHz operating frequency range (Oscillation frequency is settable by external components)
- -40 to 85°C operating temperature range
- Oscillator capacitors C_G, C_D built-in (BN×H version only)
- lacktriangle Cutoff frequency setting using external feedback resistor R_{fo}
- Output drive capability
 - $8mA (V_{DD} = 2.7V)$
 - $16\text{mA} (V_{DD} = 4.5V)$
- Output three-state function built-in
 - High impedance output in standby mode
- CMOS output duty level (1/2VDD)
- Molybdenum-gate CMOS process
- Package: SOT23-6 (SM5023×××H)

PACKAGE DIMENSIONS

(Unit: mm)



APPLICATIONS

■ DIP-type crystal oscillator modules

SERIES CONFIGURATION

	Operating	Recommended	(Oscillator circ	cuit constant	S	Output	Standby mode		
1	Supply voltage	operating frequency	am ratio	Built-in capacitance				Oscillator	Output	
	range [V]	range ¹ [MHz]	gm ratio	C _G [pF]	C _D [pF]	Rf [kΩ]	duty level	Oscillator	state	
SM5023BNDH	2.7 to 3.6	22 to 70	22 to 70	3	8	15	_	CMOS	Operation	Hi-Z
SIVISUZSBINDIT	4.5 to 5.5	22 10 70	3				CIVIOS	Operation	1 II-Z	
SM5023BNEH	2.7 to 3.6	50 to 70	4	8	12	-	CMOS	Operation	Hi-Z	
SM5023CNDH	2.7 to 3.6	4 + 20	3		_		CMOS	Operation	Hi-Z	
SINIDUZOCINDH	4.5 to 5.5	4 to 70	٥	_	_	_	CIVIOS	Operation	П-Z	

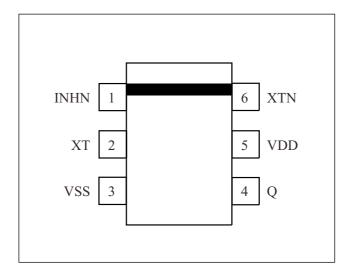
The 3rd overtone frequency range using an external resistor to set the cutoff frequency. The recommended operating frequency is a yardstick value derived from the crystal used for NPC characteristics authentication. However, the oscillator frequency band is not guaranteed. Specifically, the characteristics can vary greatly due to crystal characteristics and mounting conditions, so the oscillation characteristics of components must be carefully evaluated.

ORDERING INFORMATION

Device	Package
SM5023×××H	SOT23-6

PINOUT

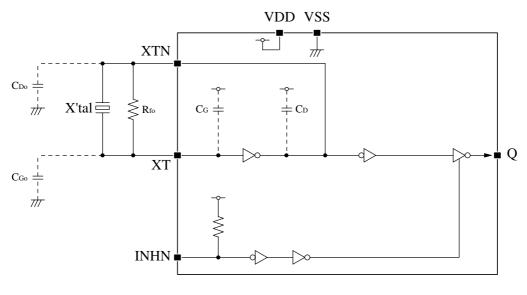
(Top view)



PIN DESCRIPTION

Name	I/O	Description				
INHN	I	Output state control input. F Pull-up resistor built-in.	Output state control input. High impedance when LOW. Pull-up resistor built-in.			
XT	I	Amplifier input	Crystal connection pins.			
XTN	0	Amplifier output	Crystal is connected between XT and XTN.			
VSS	-	Ground				
Q	0	Output. f _O (XT pin input freq	Output. f _O (XT pin input frequency)			
VDD	-	Supply voltage				

BLOCK DIAGRAM



INHN = LOW active

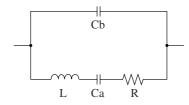
FUNCTIONAL DESCRIPTION

Standby Function

When INHN goes LOW, the oscillator output on Q becomes high impedance.

INHN	Q	Oscillator
HIGH (or open)	f _O	Normal operation
LOW	High impedance	Normal operation

Current consumption and Output waveform with NPC's standard crystal



f [MHz]	R [Ω]	L [mH]	Ca [fF]	Cb [pF]
30	18.62	16.24	1.733	5.337
40	20.53	11.34	1.396	3.989
50	22.17	7.40	1.370	4.105
60	22.20	5.05	1.388	4.226
70	25.42	4.18	1.254	5.170

SPECIFICATIONS

Absolute Maximum Ratings

 $V_{SS} = 0V$

Parameter	Symbol	Rating	Unit
Supply voltage range	V _{DD}	-0.5 to +7.0	V
Input voltage range	V _{IN}	-0.5 to V _{DD} + 0.5	V
Output voltage range	V _{OUT}	-0.5 to V _{DD} + 0.5	V
Operating temperature range	T _{opr}	-40 to +85	°C
Storage temperature range	T _{STG}	-55 to +125	°C
Output current	I _{OUT}	20	mA
Power dissipation	P _D	250	mW

Recommended Operating Conditions

3V operation: SM5023BNDH, BNEH, CNDH

 $V_{SS} = 0V$, $f \le 70MHz$, $C_L \le 15pF$ unless otherwise noted.

Parameter	Symbol	Rating			Unit
Operating supply voltage	V _{DD}	2.7	-	3.6	V
Input voltage	V _{IN}	V _{SS}	-	V _{DD}	V
Operating temperature	T _{OPR}	-20	_	+80	°C

5V operation: SM5023BNDH, CNDH

$$\begin{split} &V_{SS}=0V,\,f\leq 50MHz,\,C_L\leq 50pF \text{ unless otherwise noted.}\\ &V_{SS}=0V,\,f\leq 70MHz,\,C_L\leq 15pF \text{ unless otherwise noted.} \end{split}$$

Parameter	Symbol	Rating			Unit
Operating supply voltage	V _{DD}	4.5	-	5.5	V
Input voltage	V _{IN}	V _{SS}	-	V _{DD}	V
Operating temperature	T _{OPR}	-40	-	+85	°C

Electrical Characteristics

3V operation: SM5023BNDH, BNEH, CNDH

 $V_{\rm DD}$ = 2.7 to 3.6V, $V_{\rm SS}$ = 0V, Ta = -20 to +80°C unless otherwise noted.

Parameter	Cumbal	Condition	Rating			Unit	
Parameter	Symbol	Condition			typ	max	Unit
HIGH-level output voltage	V _{OH}	Q: Measurement cct 1, V _{DD} = 2.7V, I _{OH} = 8	mA	2.1	2.4	-	٧
LOW-level output voltage	V _{OL}	Q: Measurement cct 2, V _{DD} = 2.7V, I _{OL} = 8	mA	-	0.3	0.5	٧
HIGH-level input voltage	V _{IH}	INHN		2.0	-	-	٧
LOW-level input voltage	V _{IL}	INHN		-	-	0.5	٧
	I _Z	Q: Measurement cct 2, INHN = LOW, V _{DD} = 3.3V	$V_{OH} = V_{DD}$	-	-	10	μΑ
Output leakage current			V _{OL} = V _{SS}	-	-	10	μΑ
Current consumption	I _{DD}	Measurement cct 3, load cct 1, INHN = open, C _L = 15pF, f = 70MHz		-	15	30	mA
INHN pull-up resistance	R _{UP}	Measurement cct 4		25	100	250	kΩ
	C _G	Design value. A monitor pattern on a wafer is tested.	SM5023BNDH SM5023BNEH	7.44	8	8.56	pF
Built-in capacitance	C _D Design value. A monitor pattern on a wafer is tested.	Design value.	SM5023BNDH	13.95	15	16.05	pF
		SM5023BNEH	11.16	12	12.84	pF	

5V operation: SM5023BNDH, CNDH

 $V_{\rm DD}$ = 4.5 to 5.5V, $V_{\rm SS}$ = 0V, Ta = -40 to +85°C unless otherwise noted.

Parameter	Cumbal	Condition		Rating		Unit	
Parameter	Symbol	Condition	min	typ	max	Unit	
HIGH-level output voltage	V _{OH}	Q: Measurement cct 1, V _{DD} = 4.5V, I _{OH} = 1	6mA	3.9	4.2	-	٧
LOW-level output voltage	V _{OL}	Q: Measurement cct 2, V _{DD} = 4.5V, I _{OL} = 1	6mA	-	0.3	0.5	٧
HIGH-level input voltage	V _{IH}	INHN		2.0	-	ı	٧
LOW-level input voltage	V _{IL}	INHN		-	-	0.8	٧
	IZ	Q: Measurement cct 2, INHN = LOW, V _{DD} = 5.5V	$V_{OH} = V_{DD}$	-	-	10	μΑ
Output leakage current			V _{OL} = V _{SS}	-	-	10	μΑ
Current concumption	I _{DD1}	Measurement cct 3, load cct 1,	C _L = 15pF f = 70MHz	_	20	40	mA
Current consumption	I _{DD2}	NHN = open	C _L = 50pF f = 50MHz	_	25	50	mA
INHN pull-up resistance	R _{UP}	Measurement cct 4	•	25	100	250	kΩ
Duilt in conscitones	C _G	Design value. A monitor pattern on a wafer is tested.	SM5023BNDH	7.44	8	8.56	pF
Built-in capacitance	C _D	Design value. A monitor pattern on a wafer is tested.	SM5023BNDH	13.95	15	16.05	pF

Switching Characteristics

3V operation: SM5023BNDH, BNEH, CNDH

 $V_{\rm DD}$ = 2.7 to 3.6V, $V_{\rm SS}$ = 0V, Ta = -20 to +80°C unless otherwise noted.

Parameter	Symbol	Symbol Condition		Rating		
raiailletei	Symbol			typ	max	Unit
Output rise time	t _{r1}	Measurement cct 5, load cct 1, $0.1V_{DD}$ to $0.9V_{DD}$, C_L = 15pF	-	2.5	5	ns
Output fall time	t _{f1}	Measurement cct 5, load cct 1, $0.9V_{DD}$ to $0.1V_{DD}$, C_{L} = 15pF	-	2.5	5	ns
Output duty cycle ¹	Duty1	Measurement cct 5, load cct 1, V_{DD} = 3.0V, Ta = 25°C, C_L = 15pF, f \leq 70MHz	45	-	55	%
Output disable delay time	t _{PLZ}	Measurement cct 5, load cct 1, V _{DD} = 3.0V, Ta = 25°C,	-	-	100	ns
Output enable delay time	t _{PZL}	C _L = 15pF	-	-	100	ns

^{1.} The duty cycle characteristic is checked the sample chips of each production lot.

5V operation: SM5023BNDH, CNDH

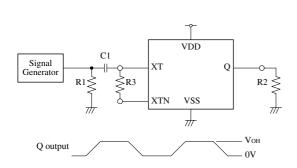
 $V_{\rm DD}$ = 4.5 to 5.5V, $V_{\rm SS}$ = 0V, Ta = -40 to +85°C unless otherwise noted.

Parameter	Cumbal	Condition		Rating			Limit
Parameter	Symbol	Condition		min	typ	max	Unit
Output rise time	t _{r1}	Measurement cct 5, load cct 1,	C _L = 15pF	-	1.5	3	
Output rise time	t _{r2}	0.1V _{DD} to 0.9V _{DD}	C _L = 50pF	-	3	6	ns
Outside fall for a	t _{f1}	Measurement cct 5, load cct 1,	C _L = 15pF	-	1.5	3	no
Output fall time	t _{f2}	0.9V _{DD} to 0.1V _{DD}	C _L = 50pF	-	3	6	ns
Output duty avala	Duty1	Measurement cct 5, load cct 1,	C _L = 15pF f ≤ 70MHz	45	-	55	%
Output duty cycle ¹	Duty2	V _{DD} = 5.0V, Ta = 25°C	C _L = 50pF f ≤ 50MHz	45	-	55	%
Output disable delay time	t _{PLZ}	Measurement cct 5, load cct 1, V _{DD} = 5.0V, Ta = 25°C, C _L = 15pF		-	-	100	ns
Output enable delay time	t _{PZL}			-	-	100	ns

^{1.} The duty cycle characteristic is checked the sample chips of each production lot.

MEASUREMENT CIRCUITS

Measurement cct 1



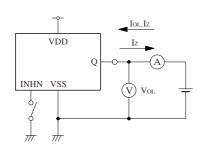
2.0Vp-p, 10MHz sine wave input signal (3V operation) 3.5Vp-p, 10MHz sine wave input signal (5V operation)

C1: 0.001μF R1: 50Ω

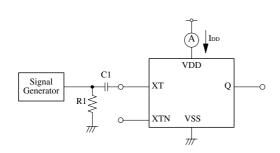
R2: 263Ω (3V operation) 244Ω (5V operation)

R3: 100kΩ

Measurement cct 2



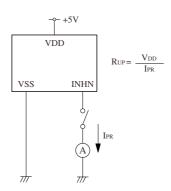
Measurement cct 3



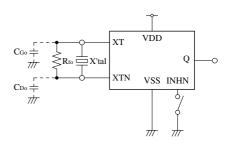
2.0Vp-p, 70MHz sine wave input signal (3V operation) 3.5Vp-p, 70MHz sine wave input signal (5V operation)

C1: 0.001μF R1: 50Ω

Measurement cct 4



Measurement cct 5



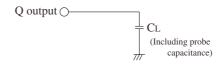
Crystal oscillation

 R_{fo} : 1.5k Ω (3V, 70MHz operation) 3.9k Ω (5V, 70MHz operation)

5.6kΩ (5V, 50MHz operation)

SM5023CNDH: $C_{Go} = 8pF$, $C_{Do} = 15pF$

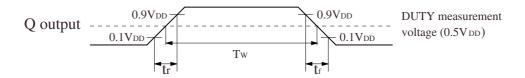
Load cct 1



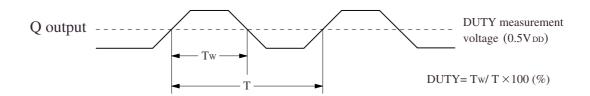
 $\begin{aligned} &C_{L} = 15 \text{pF: } t_{r1},\, t_{f1},\, \text{Duty1, } I_{DD1} \\ &C_{L} = 50 \text{pF: } t_{r2},\, t_{f2},\, \text{Duty2, } I_{DD2} \end{aligned}$

Switching Time Measurement Waveform

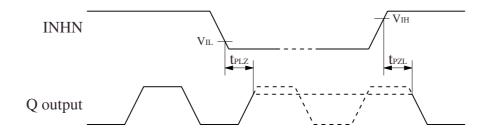
Output duty level, t_r, t_f



Output duty cycle



Output Enable/Disable Delay



 $INHN \ input \ waveform \ tr = tf \le 10ns$

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SEIKO NPC CORPORATION

1-9-9, Hatchobori, Chuo-ku, Tokyo 104-0032, Japan Telephone: +81-3-5541-6501 Facsimile: +81-3-5541-6510 http://www.npc.co.jp/ Email: sales@npc.co.jp

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